

18N65

Power MOSFET

18A, 650V N-CHANNEL
POWER MOSFET

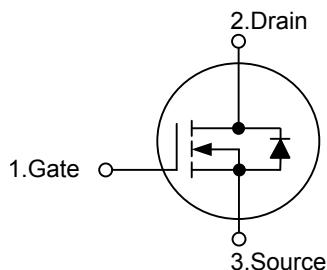
■ DESCRIPTION

The UTC **18N65** uses UTC's advanced proprietary, planar stripe, DMOS technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with low gate voltages. This device is suitable for use as a load switch or in PWM applications.

■ FEATURES

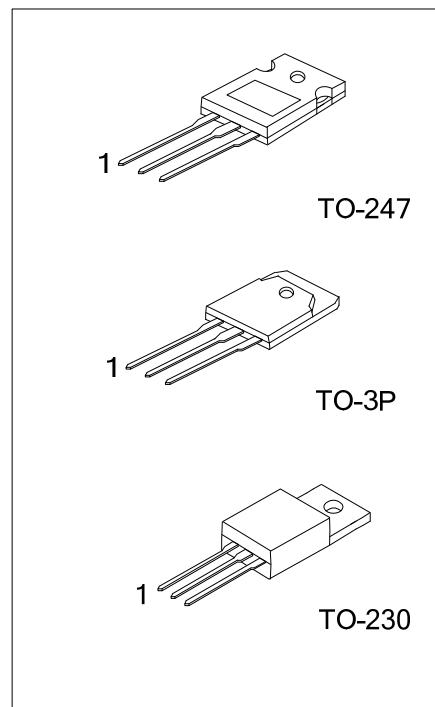
- * $R_{DS(ON)} \leq 0.5\Omega$ @ $V_{GS} = 10$ V
- * Ultra Low Gate Charge (Typical 50nC)
- * Low Reverse Transfer Capacitance ($C_{RSS} =$ Typical 23pF)
- * Fast Switching Capability
- * Avalanche Energy Specified
- * Improved dv/dt Capability, High Ruggedness

■ SYMBOL



■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
18N65L-T3P-T	18N65G-T3P-T	TO-3P	G	D	S	Tube
18N65L-T47-T	18N65G-T47-T	TO-247	G	D	S	Tube
18N65L-TC3-T	18N65G-TC3-T	TO-230	G	D	S	Tube



18N65L-T3P-T



(1)Packing Type

(2)Package Type

(3)Lead Free

(1) T: Tube

(2) T3P:TO-3P, T47: TO-247, TC3: TO-230

(3) L: Lead Free, G: Halogen Free

■ ABSOLUTE MAXIMUM RATINGS ($T_c = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	650	V
Gate-Source Voltage		V_{GSS}	± 30	V
Continuous Drain Current		I_D	18	A
Pulsed Drain Current		I_{DM}	45	A
Avalanche Current		I_{AR}	18	A
Avalanche Energy	Single Pulsed	E_{AS}	1000 (Note 2)	mJ
	Repetitive	E_{AR}	30	
Peak Diode Recovery dv/dt		dv/dt	10	V/ns
Power Dissipation	TO-3P	P_D	390	W
	TO-247		357	W
	TO-230		360	W
Junction Temperature		T_J	150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Note: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. $L=6.18\text{mH}$, $I_{AS}=18\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\Omega$, Starting $T_J=25^\circ\text{C}$

■ THERMAL DATA

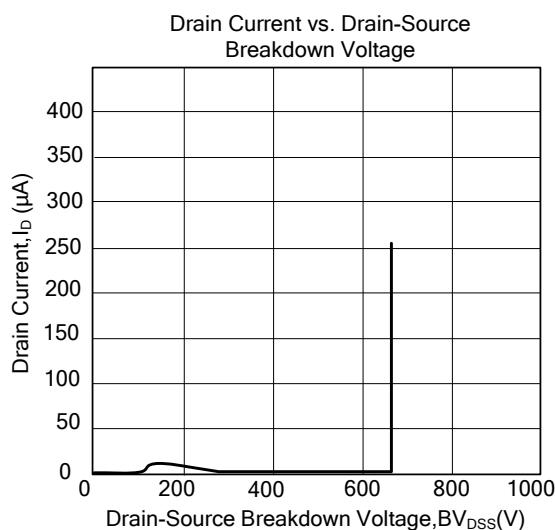
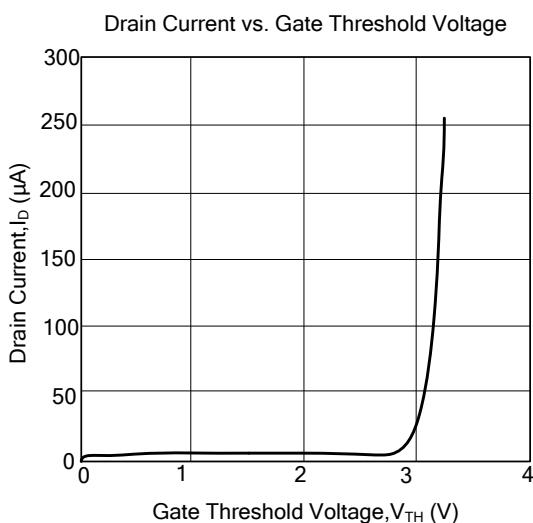
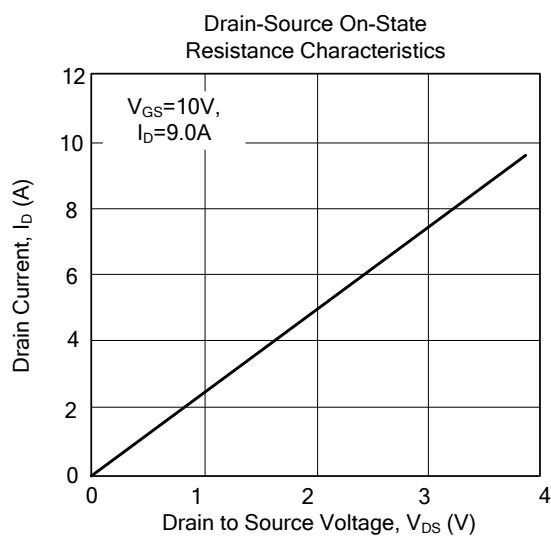
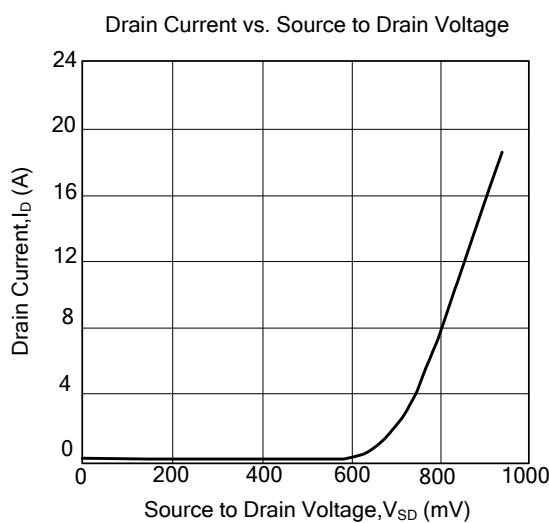
PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-3P	θ_{JA}	30	$^\circ\text{C/W}$
	TO-247		40	$^\circ\text{C/W}$
	TO-230		62.5	$^\circ\text{C/W}$
Junction to Case	TO-3P	θ_{JC}	0.32	$^\circ\text{C/W}$
	TO-247		0.35	$^\circ\text{C/W}$
	TO-230		0.5	$^\circ\text{C/W}$

■ ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	650			V
Drain-Source Leakage Current	$I_{\text{DS}}^{\text{SS}}$	$V_{\text{DS}}=650\text{V}, V_{\text{GS}}=0\text{V}$			25	μA
Gate-Body Leakage Current	I_{GSS}	$V_{\text{DS}}=0\text{V}, V_{\text{GS}}=\pm 30\text{V}$			± 100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{\text{GS}(\text{TH})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	2.0		4.0	V
Static Drain-Source On-Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=10\text{V}, I_{\text{D}}=9\text{A}$ (Note)		0.36	0.5	Ω
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	$V_{\text{DS}}=25\text{V}, V_{\text{GS}}=0\text{V}, f=1\text{MHz}$		2500		pF
Output Capacitance	C_{OSS}			280		pF
Reverse Transfer Capacitance	C_{RSS}			23		pF
SWITCHING PARAMETERS						
Turn-ON Delay Time	$t_{\text{D}(\text{ON})}$	$V_{\text{GS}}=10\text{V}, V_{\text{DS}}=0.5V_{\text{DSS}}, I_{\text{D}}=18\text{A}, R_{\text{G}}=5\Omega$ (External)		21		ns
Turn-ON Rise Time	t_{R}			60		ns
Turn-OFF Delay Time	$t_{\text{D}(\text{OFF})}$			62		ns
Turn-OFF Fall-Time	t_{F}			60		ns
Total Gate Charge	Q_{G}	$V_{\text{GS}}=10\text{V}, V_{\text{DS}}=0.8V_{\text{DSS}}, I_{\text{D}}=18\text{A}$		50		nC
Gate Source Charge	Q_{GS}			15		nC
Gate Drain Charge	Q_{GD}			18		nC
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Drain-Source Diode Forward Voltage	V_{SD}	$I_{\text{F}}=I_{\text{S}}, V_{\text{GS}}=0\text{V}$ (Note)			1.5	V
Maximum Continuous Drain-Source Diode Forward Current	I_{S}	$V_{\text{GS}}=0\text{V}$			18	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}	Repetitive			54	A
Reverse Recovery Time	t_{rr}	$V_{\text{GS}}=0\text{V}, \frac{dI_{\text{F}}}{dt}=100\text{A}/\mu\text{s}, I_{\text{S}}=18\text{A}, V_{\text{R}}=100\text{V}$			200	ns
Reverse Recovery Charge	Q_{RR}			0.8		μC

Note: Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.

■ TYPICAL CHARACTERISTICS



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